

SANYO

No.695G

2SK242

N-Channel Junction Silicon FET

High-Frequency General-Purpose Amp Applications**Features**

- Ultrasmall-sized package permitting 2SK242-applied sets to be made small and slim.
- Small Crss (Crss=0.04pF typ).

Absolute Maximum Ratings at Ta=25°C

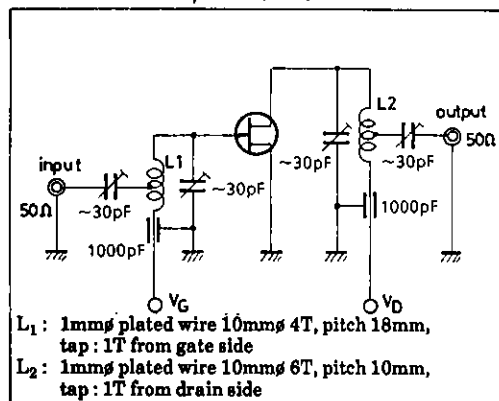
			unit
Gate-to-Drain Voltage	V_{GDO}	-20	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	150	mW
Junction Temperature	T_j	125	°C
Storage Temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics at Ta=25°C

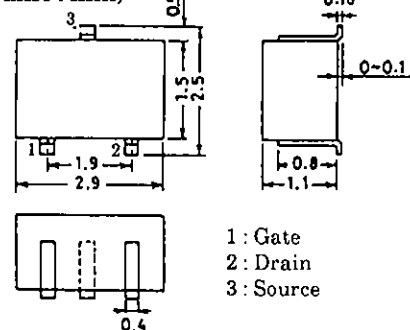
			min	typ	max	unit
G-D Breakdown Voltage	$V_{(BR)GDO}$	$I_G = -10\mu A$	-20			V
Gate Cutoff Current	I_{GSS}	$V_{GS} = -0.5V, V_{DS} = 0$			-10	nA
Drain Current	I_{DSS}	$V_{DS} = 5V, V_{GS} = 0$	0.6※		12.0※	mA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5V, I_D = 10\mu A$			-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	(1) $V_{DS} = 5V, V_{GS} = 0, f = 1kHz$	2.0	6.0		mS
		(2) $V_{DS} = 5V, V_{GS} = 0, f = 100MHz$	2.0	6.0		mS
Input Capacitance	C_{iss}	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$		4.0		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$		0.04	0.15	pF
Output Capacitance	C_{oss}	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$		4.0		pF
Power Gain	PG	$V_{DS} = 5V, V_{GS} = 0, f = 100MHz$		24		dB
Noise Figure	NF	See specified Test Circuit.		3.5	6.0	dB

※ : The 2SK242 is classified by I_{DSS} as follows : (unit : mA)

0.6	2	1.5	1.2	3	3.0	2.5	4	6.0	5.0	5	12.0
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Note) Marking : T I_{DSS} rank : 2, 3, 4, 5**PG, NF Test Circuit****Package Dimensions 2024B**

(unit : mm)

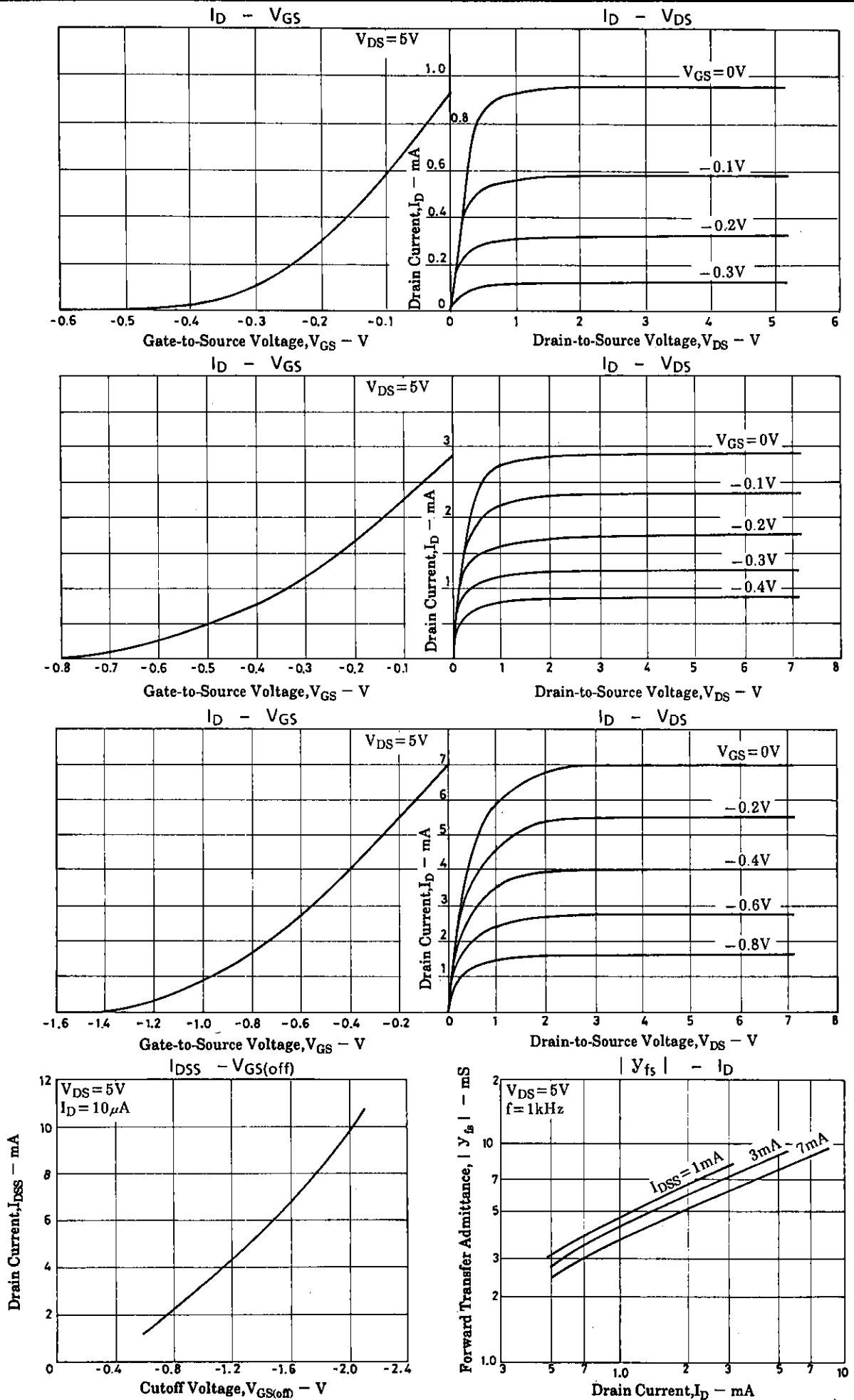


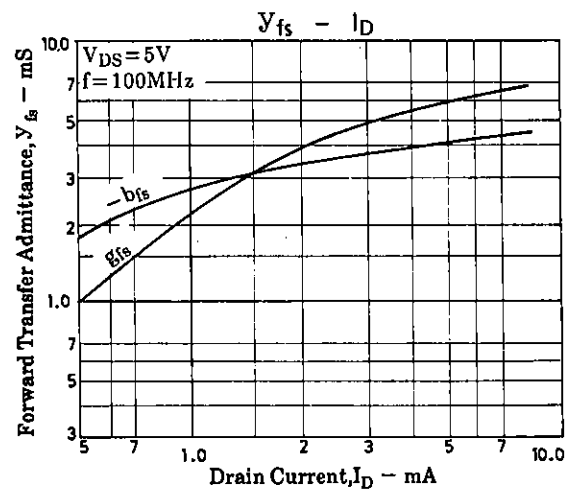
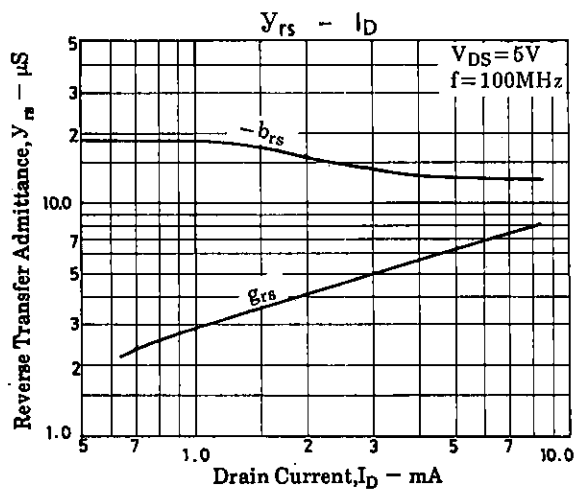
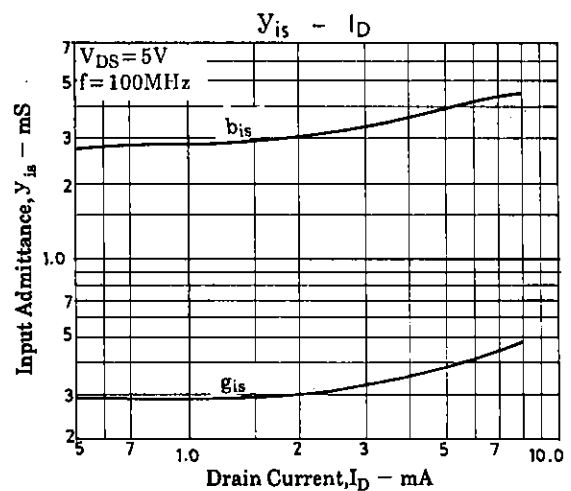
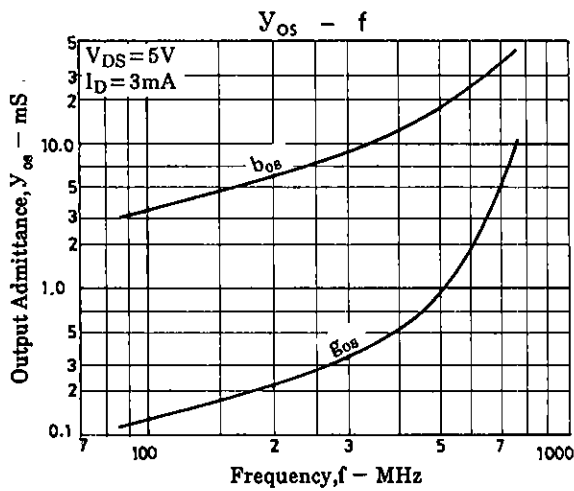
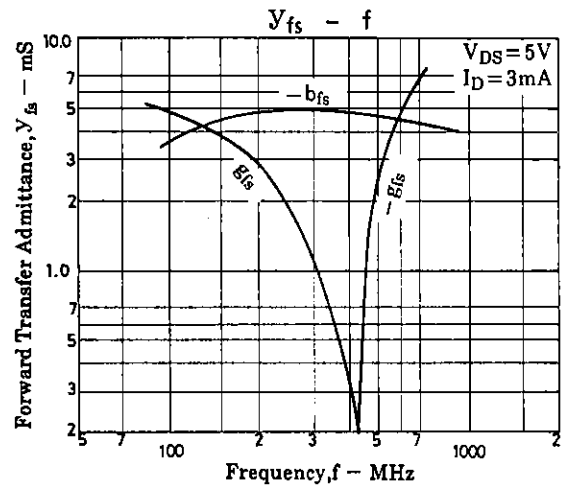
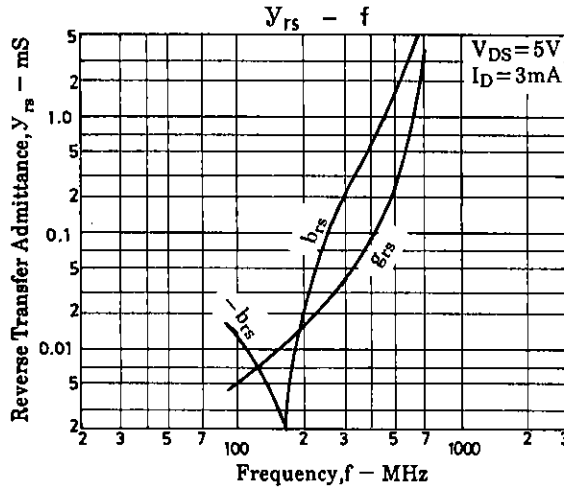
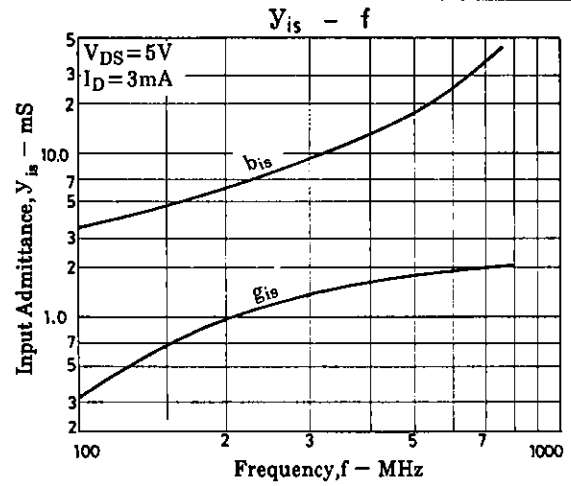
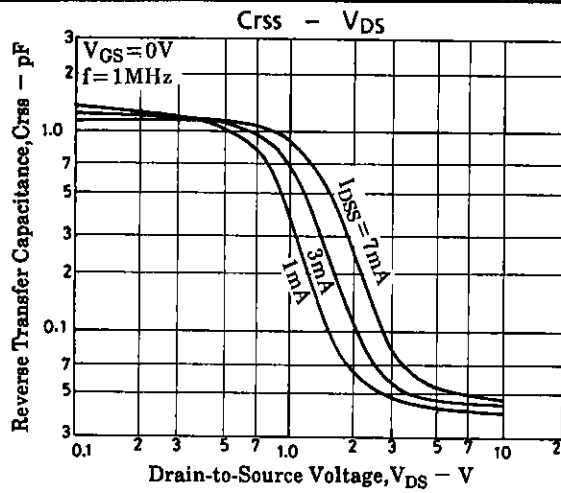
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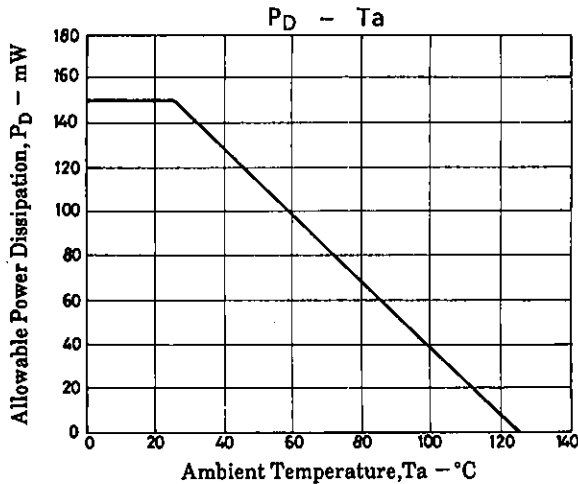
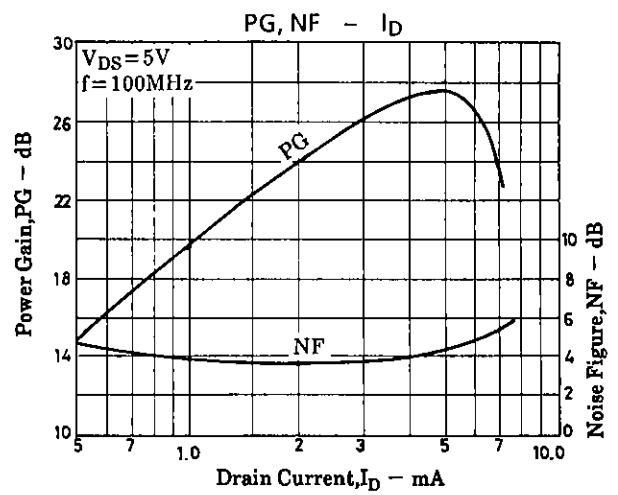
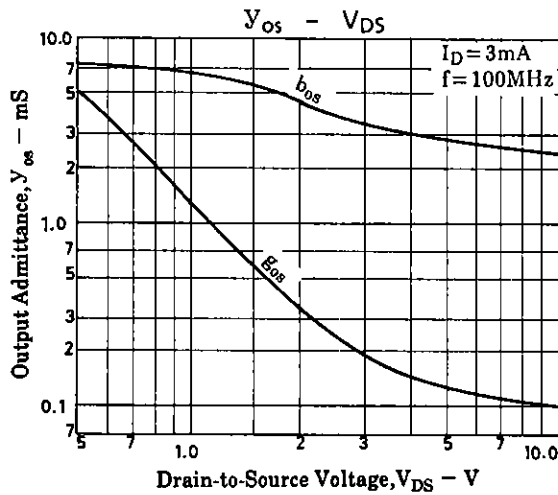
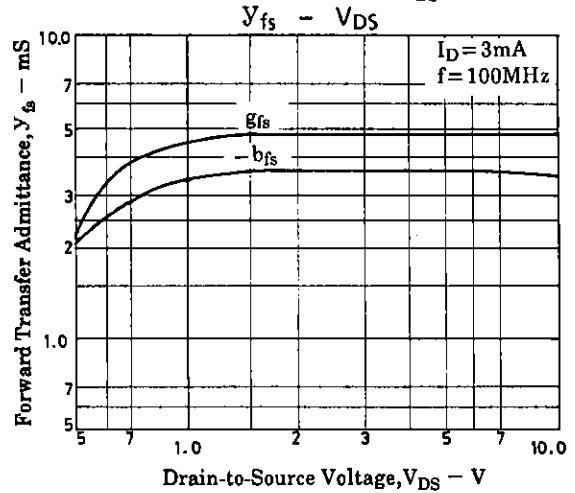
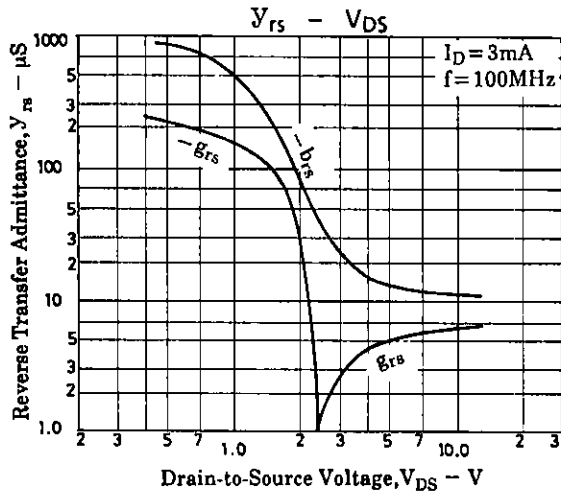
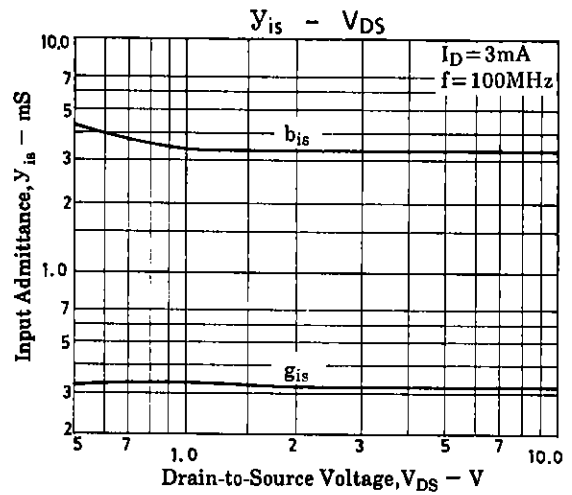
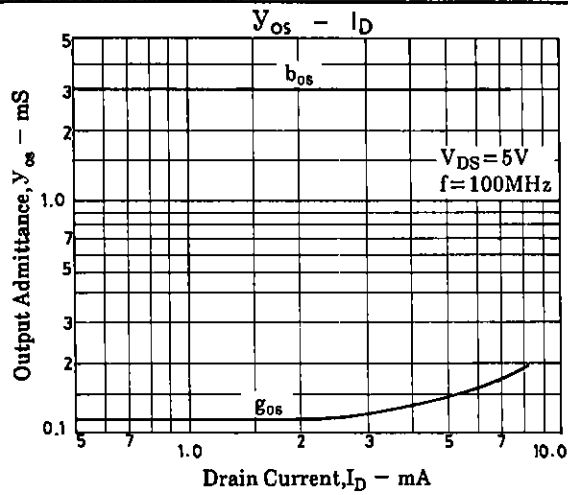
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2SK242







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